

• General Description

The ZMD68310S combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Dual DIE in one package

• Application

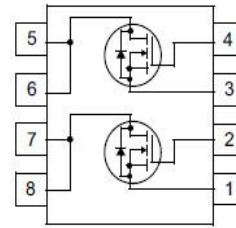
- Power Management in Notebook Computer,
- Portable Equipment and Battery Powered Systems

• Ordering Information:

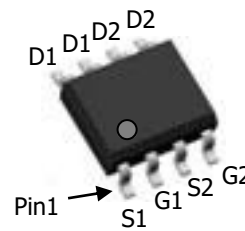
Part NO.	ZMD68310S
Marking	ZMD68310
Packing Information	REEL TAPE
Basic ordering unit (pcs)	4000

• Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	20	V
Continuous Drain Current	$I_D @ T_C = 25^\circ\text{C}$	5	A
	$I_D @ T_C = 75^\circ\text{C}$	3.8	A
	$I_D @ T_C = 100^\circ\text{C}$	3.1	A
Pulsed Drain Current ^①	I_{DM}	15	A
Total Power Dissipation	$P_D @ T_C = 25^\circ\text{C}$	3.6	W
Total Power Dissipation	$P_D @ T_A = 25^\circ\text{C}$	0.69	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to 150	$^\circ\text{C}$
Single Pulse Avalanche Energy	E_{AS}	25	mJ

• Product Summary


$V_{DS1} = 30\text{V}$
 $V_{DS2} = 30\text{V}$
 $R_{DS(ON)1} = 18\text{m}\Omega$
 $R_{DS(ON)2} = 18\text{m}\Omega$
 $I_{D1} = 5\text{A}$
 $I_{D2} = 5\text{A}$



SOP8



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2.5	$^{\circ}C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	70	$^{\circ}C/W$
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	$^{\circ}C$

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=5A$		18	24	m Ω
		$V_{GS}=4.5V, I_D=5A$		26	32	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=1A$		5		S
Source-drain voltage	V_{SD}	$I_S=5A$			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz$	-	383	-	pF
Output capacitance	C_{oss}		-	70	-	
Reverse transfer capacitance	C_{rss}		-	40	-	

•Gate Charge characteristics($T_a = 25^{\circ}C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 25V$	-	4	-	nC
Gate - Source charge	Q_{gs}	$I_D = 5A$	-	1.3	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 10V$	-	2	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Fig.1 Power Dissipation

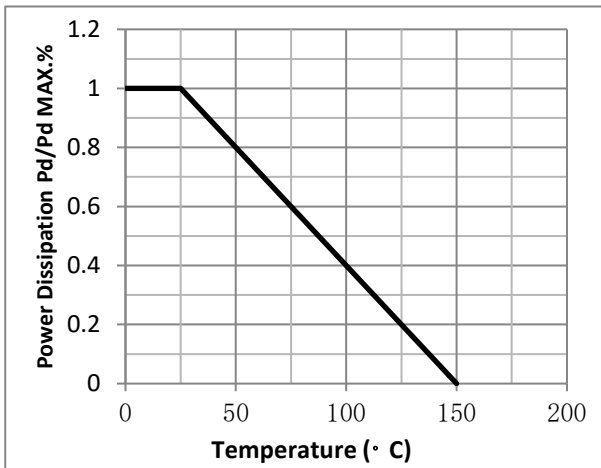


Fig.2 Typical output Characteristics

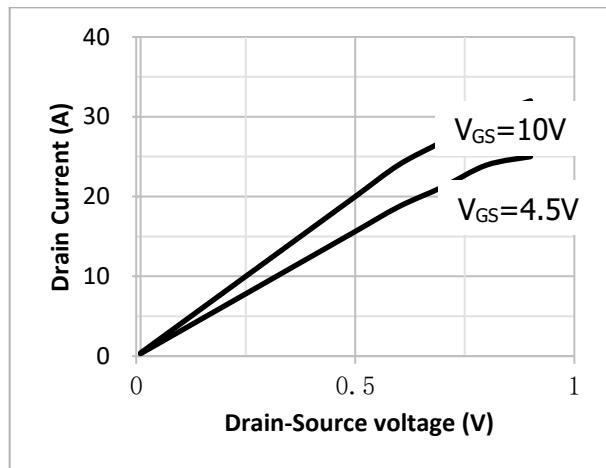


Fig.3 Threshold Voltage V.S Junction Temperature

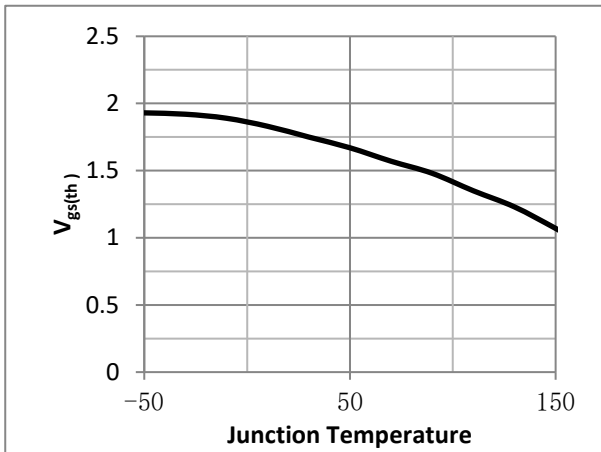


Fig.4 Resistance V.S Drain Current

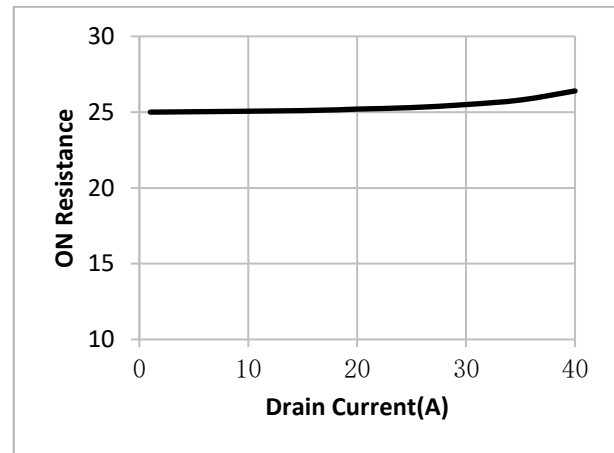


Fig.5 On-Resistance VS Gate Source Voltage

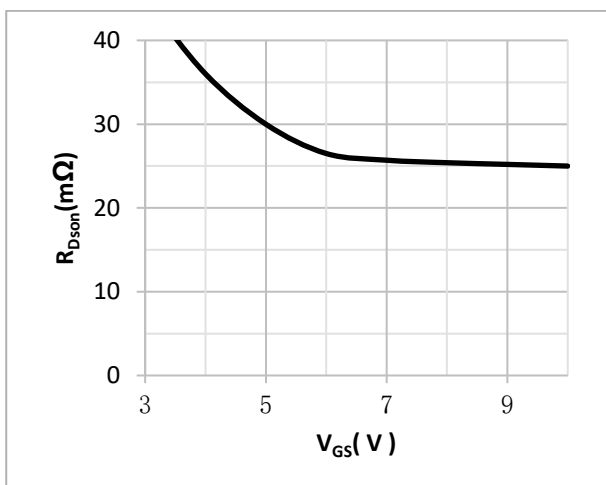


Fig.6 On-Resistance V.S Junction Temperature

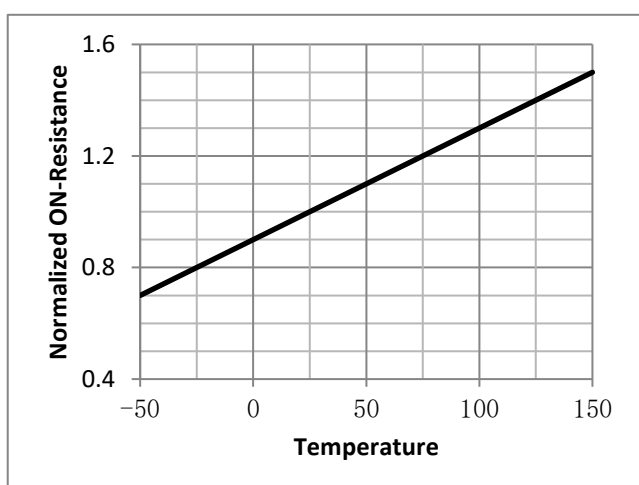


Fig.7 Switching Time Measurement Circuit

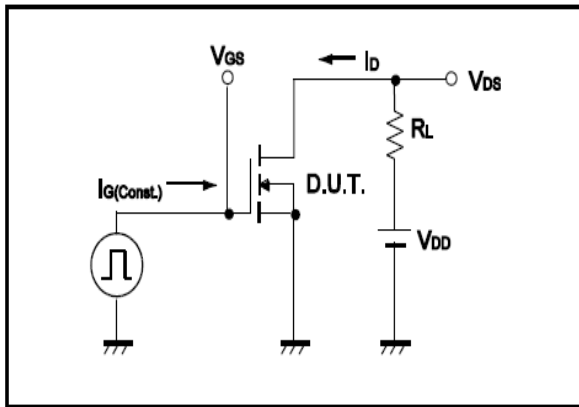


Fig.8 Gate Charge Waveform

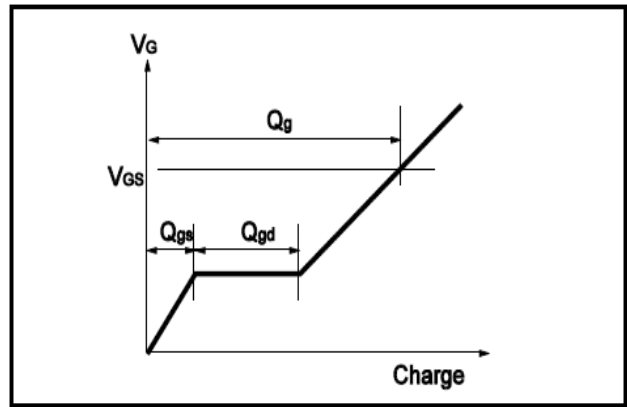


Fig.9 Switching Time Measurement Circuit

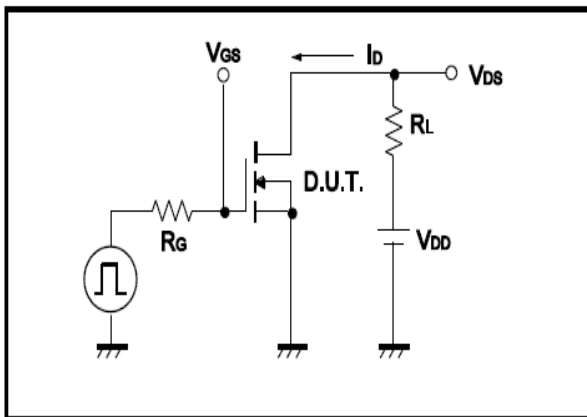


Fig.10 Gate Charge Waveform

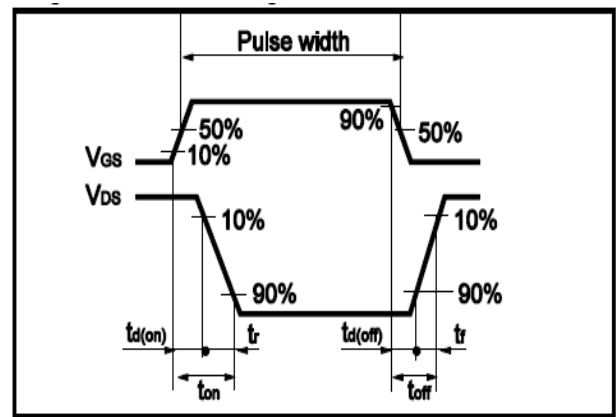


Fig.11 Avalanche Measurement Circuit

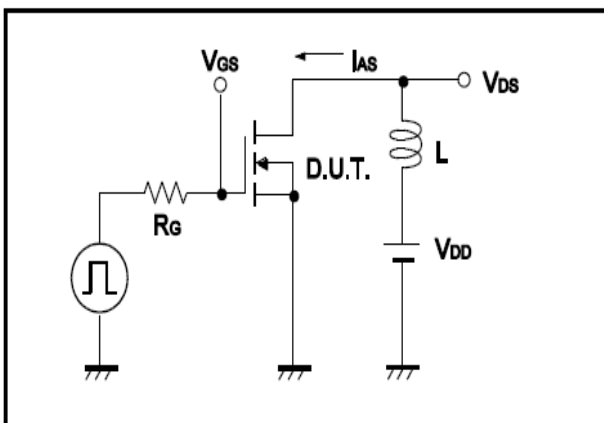
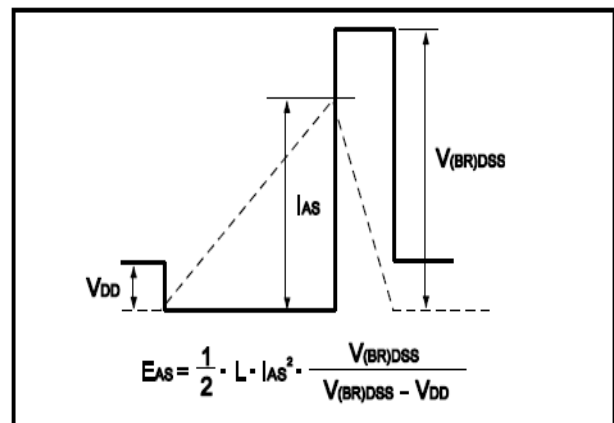


Fig.12 Avalanche Waveform



●Dimensions(SOP8)

Unit: mm

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.25	C	1.30		1.75
A1	0.37		0.49	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.10	0.20	0.23
B1	3.80		4.10	D		1.05	
B2		5.00		D1	0.40		0.62

